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REIN

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

A. NISHIMURA et al

Serial No.

Filed: June 26, 2001

For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE  
AND MANUFACTURE THEREOF

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows.

IN THE CLAIMS

Rewrite claims 3, 7, 9, and 12-14 as follows:

A1  
3. (Amended) The semiconductor integrated circuit device according to claim 1, wherein said conductive layers are metal wirings, said insulating film is formed on said each metal wiring, and an insulating film is further formed below said each metal wiring.

A2  
7. (Amended) The semiconductor integrated circuit device according to claim 1, wherein said testing pads are placed just above said terminals corresponding thereto.

A3 SUB B4  
9. (Amended) The semiconductor integrated circuit device according to claim 1, wherein said testing pads extend on said insulating film.